

EB-BB-500Q-0808-03

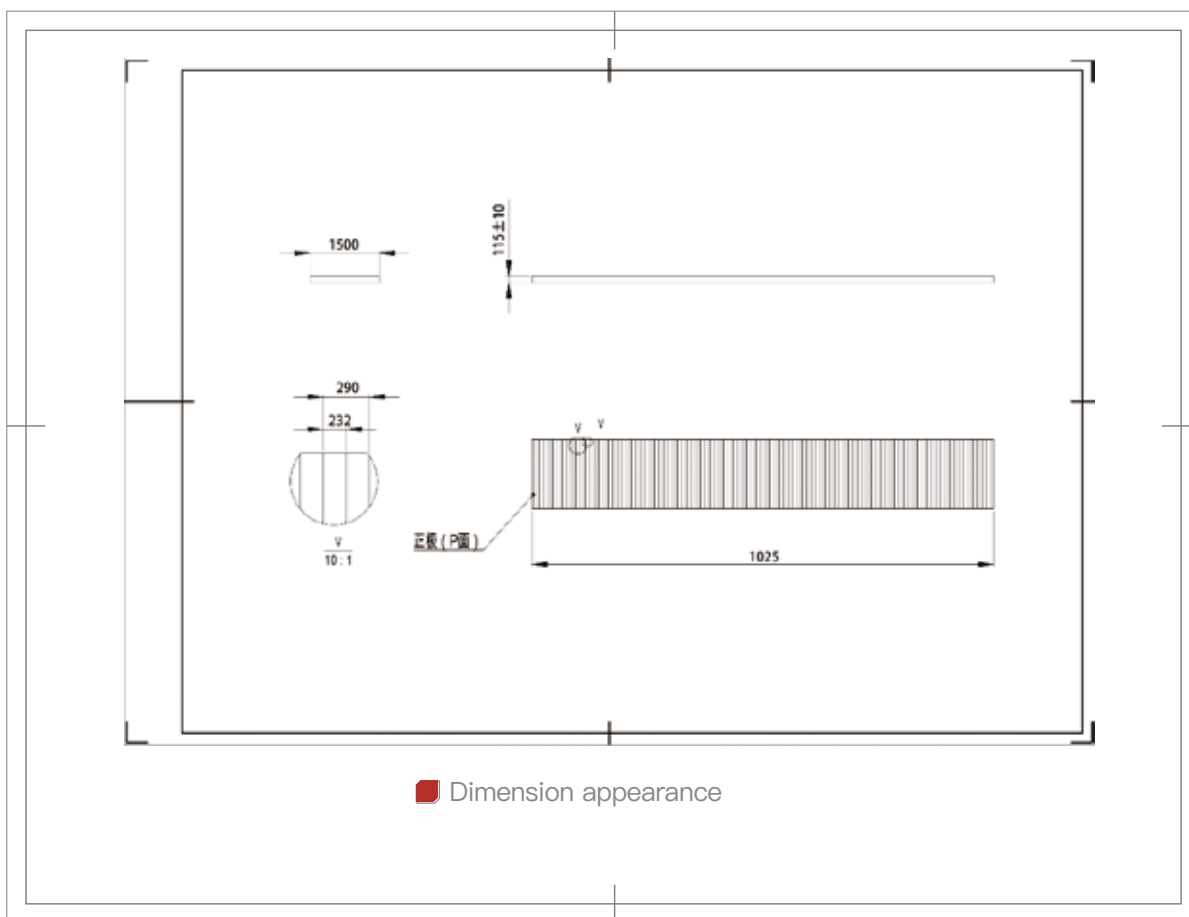
HIGH POWER DIODE BAR LASER CHIP



	Unit	Min	Typ	Max
Optical				
Center Wavelength	nm		808	
Wavelength Tolerance	nm		±3	
Output Power	W	500		
Fast-axis Divergence	Deg		65	75
Slow-axis Divergence	Deg		8	
Spectral Width (FWHM)	nm		3.5	4
Polarization	TM/TE		TE	
Wavelength Temperature Coefficient	nm/°C		0.28	
Electrical				
Power Conversion Efficiency	%	55	58	
Slope Efficiency	W/A		1.25	
Threshold Current	A		24	
Operating Current	A		430	440
Operating Voltage	V		2	
Pulse Width	us		200	500
Pulse frequency	Hz		400	
Pulse duty cycle	%		8	10
Geometric Size				
Number of Emitters	#		34	
Emitter Width	μm		232	
Emitter Pitch	μm		290	
Fill Factor	%		80	
Cavity Length	mm		1.5	
Bar Thickness	μm	105	115	125
Bar Length	mm	10.00	10.05	10.10
Thermal				
Operating Temperature	°C		25	
Storage Temperature	°C		-40~80	
Flow Velocity	L/min		0.25	

Remarks

- 1.Explanation of Item Number: EB (Everbright In Short) – BB (Bare Bar) –500Q (Output Power) – 0808 (Center Wavelength) – 03 (Wavelength Tolerance)
- 2.Above Data Test at 25°C, Unless otherwise stated.
- 3.Please avoid operation and storage in the condensation enviroment. If exceed operating temperature, the device lifetime will be inpacted.
4. Lifetime reduced if exceed nominal output power.



Dimension appearance

Product Features



High Reliability



High Efficiency



High Power

Application



Industrial Pump



Laser Equipment



R&D



Biomedical



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